

Product Overview

NTLJF3117P: Single P-Channel μ Cool™ Power MOSFET with Schottky Diode - 20V -4.1A 100m Ω

For complete documentation, see the data sheet.

Power MOSFET and Schottky Diode
-20 V, -4.1 A, P-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm,
 μ Cool™ Package

Features

- FETKY™ Configuration with MOSFET plus Low Vf Schottky Diode
- μ Cool™ Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- 2x2 mm Footprint Same as SC-88 Package Design
- Independent Pinout Provides Circuit Design Flexibility
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environment
- High Current Schottky Diode: 2 A Current Rating
- This is a Pb-Free Device

Applications

- Optimized for Portable Applications
- DC-DC Buck Circuit
- Li-Ion Battery Applications
- Color Display and Camera Flash Regulators

End Products

- Cell Phones
- Digital Cameras
- Media Players

Part Electrical Specifications

| Product | Pricing (\$/Unit) | Compliance | Status | Channel Polarity | Configuration | $V_{DS}^{(BR)}$ Min (V) | V_{GS}^{Max} (V) | $V_{GS}^{(th)}$ Max (V) | I_D^{Max} (A) | P_D^{Max} (W) | $R_{DS(on)}^{n)}$ Max @ $V_{GS} = 2.5$ V (m Ω) | $R_{DS(on)}^{n)}$ Max @ $V_{GS} = 4.5$ V (m Ω) | $R_{DS(on)}^{n)}$ Max @ $V_{GS} = 10$ V (m Ω) | Q_g^{Typ} @ $V_{GS} = 4.5$ V (nC) | Q_g^{Typ} @ $V_{GS} = 10$ V (nC) | C_{iss}^{Typ} (pF) | Package Type |
|---------------|-------------------|------------------------|--------|------------------|---------------------|-------------------------|--------------------|-------------------------|-----------------|-----------------|--|--|---|-------------------------------------|------------------------------------|----------------------|--------------|
| NTLJF3117PT1G | 0.12 | Pb-free Halide free | Active | P-Channel | with Schottky Diode | -20 | 8 | 1 | 3.3 | 1.5 | 135 | 100 | - | 12.8 | 5.5 | 531 | WDFN-6 |

For more information please contact your local sales support at www.onsemi.com.

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